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## **Innovative Silicon Selected as a Finalist in EDN's 18th Annual Innovation Awards Competition**

*Z-RAM® memory technology cited as one of three finalists in the 'digital ICs, memory, and programmable logic' category*

SANTA CLARA, Calif. – February 7, 2008 – Innovative Silicon Inc. (ISi), the developer of Z-RAM® high-density memory intellectual property (IP), today announced that it has been selected from hundreds of nominations to be a finalist for this year's EDN Innovation Awards. Instituted in 1990, the Innovation Awards honor the people, products, and technologies that have shaped the semiconductor industry over the past year.

"We are extremely pleased to be named a finalist for this year's EDN Innovation Award," said Mark-Eric Jones, CEO of Innovative Silicon. "Memory has, by far, the biggest impact on the electronics industry. By offering innovative memory technology, we remain committed to helping today's leading chip manufacturers make dramatic reductions in chip costs while gaining improvements in functionality. This EDN honor is a strong endorsement of that commitment and further validates the value of our Z-RAM ultra-high-density memory IP."

ISi's had its Z-RAM technology selected in the *Digital ICs, Memory, and Programmable Logic* category – one of 21 EDN Innovation Awards categories this year. The company's Z-RAM memory technology, a true single transistor floating body memory, significantly reduces the cost of complex chips by at least 10-40 percent and gives chips more data capacity than current technology allows. By making data more easily and quickly accessible, Z-RAM increases general PC performance by providing two to four times more memory for the same cost of today's embedded DRAM and embedded SRAM technologies, or the same memory capacity for substantially less cost.

“We have our broadest set of categories in the history of our Innovation Awards program in 2007,” states EDN editorial director Maury Wright. “With specialization affecting everything from components to test equipment, our staff diligently worked to group like technologies for meaningful comparison and delivered an outstanding slate of finalists. The slate includes the range of ICs from analog to processors, development and EDA software, amazing sensors, and modular and system products including test equipment. The voters will face tough decisions but without doubt, compelling products will emerge as winners.”

During the month of February, EDN’s worldwide audience of electronics engineers and engineering managers will use an online ballot to select the ultimate winners from among the finalists. EDN’s editorial staff and Editorial Advisory Board also take part in determining the final winners. Please visit [www.EDN.com/innovation18](http://www.EDN.com/innovation18) to review each of the nominees and cast your vote. Winners will be announced at a dinner and awards ceremony on April 14, 2008 in San Jose, CA.

### **About EDN and EDN.com**

EDN serves the vital information needs of design engineers and engineering managers worldwide. EDN.com delivers a three-dimensional view of the electronics industry via news coverage, strategic business information, and in-depth technical content. ([www.edn.com](http://www.edn.com)) EDN is published by Reed Business Information ([www.reedbusiness.com/us](http://www.reedbusiness.com/us)), the largest business-to-business publisher in the U.S. and a member of the Reed Elsevier Group plc (NYSE: RUK and ENL) – a world-leading publisher and information provider.

### **About Innovative Silicon**

Innovative Silicon Inc. (ISi) delivers ultra-high density memory IP for embedded SoC, MPU and portable consumer applications requiring low power, high density and high speed. Endorsed by IEEE Spectrum Magazine in January 2007 as the winning semiconductor technology, and again in April 2007 by winning its ACE award for Emerging Technology, ISi’s Z-RAM® memory offers up to twice the density of embedded DRAM and is up to four times denser than embedded SRAM. Z-RAM memory is currently being licensed by Hynix Semiconductor for use in its DRAM chips, and is being licensed by AMD for use in its future microprocessors. The company closed its first round of VC funding in 2003, completed its first 90nm megabit Z-RAM memory designs in 2004, its first 65nm designs in 2005 and its first 45nm designs in 2006. With more than 20 patents already granted, Z-RAM’s unique single-transistor architecture is the world’s lowest cost semiconductor memory solution. The company is incorporated in the USA with R&D in Lausanne, Switzerland. For more information see [www.z-ram.com](http://www.z-ram.com).

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